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#### **Acknowledgements**

The authors acknowledge Dr. Jagdeep Shah of DARPA for funding under contract numbers W911NF-06-1-0449 and W911NF-08-1-0362. The authors also acknowledge J. L. Hoyt and M. Schmidt of MIT for discussing the localized substrate removal method as well as D. Buss, S. Yu and R. Khamankar of Texas Instruments for discussing relevant CMOS processing steps. M. Georges, J. Leu and B. Moss of MIT designed the electronic circuits contained on the die shown in Fig. 1a.